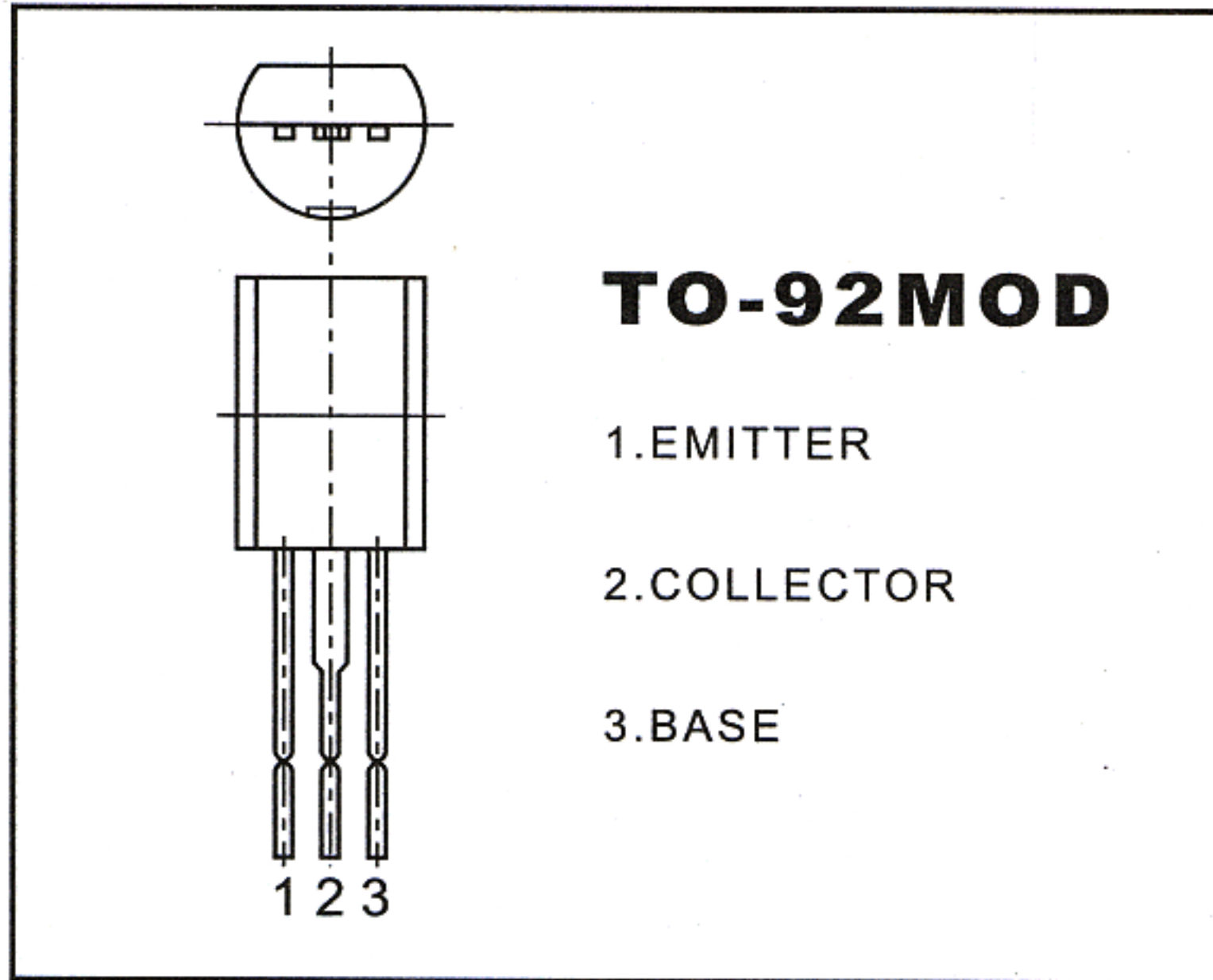


## 2SC2060 TRANSISTOR(NPN)



### FEATURES

#### Power dissipation

$P_{CM}$ : 0.75W ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : 1 A

#### Collector-base voltage

$V_{(BR)CBO}$ : 40 V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### ELECTRICAL CHARACTERISTICS

( $T_{amb}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 40 V, I_E = 0$		0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4 V, I_C = 0$		0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = 3 V, I_C = 100 mA$	80	400	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = 500 mA, I_B = 50 mA$		0.4	V